Supplemental Figures for

“Thermal Atomic Layer Etching of GaN and Ga_2O_3 Using Sequential Fluorination and Ligand-Exchange Reactions”

by Nicholas S. Johnson, Younghee Lee and Steven M. George

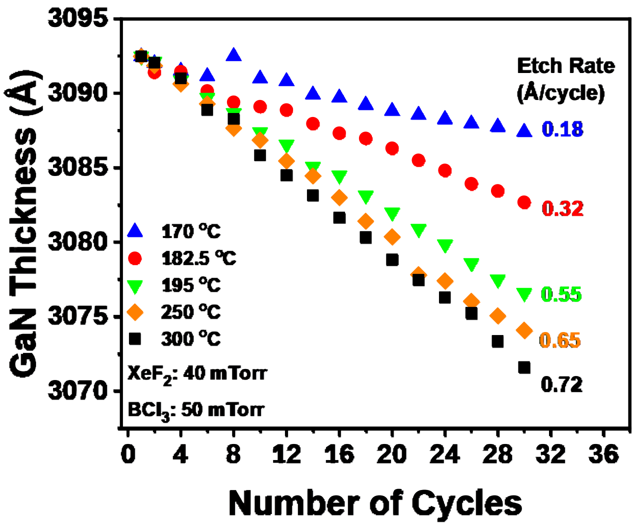

Figure 1. Spectroscopic ellipsometry measurements of GaN thickness versus number of cycles of sequential XeF_2 and BCl_3 exposures at various temperatures.

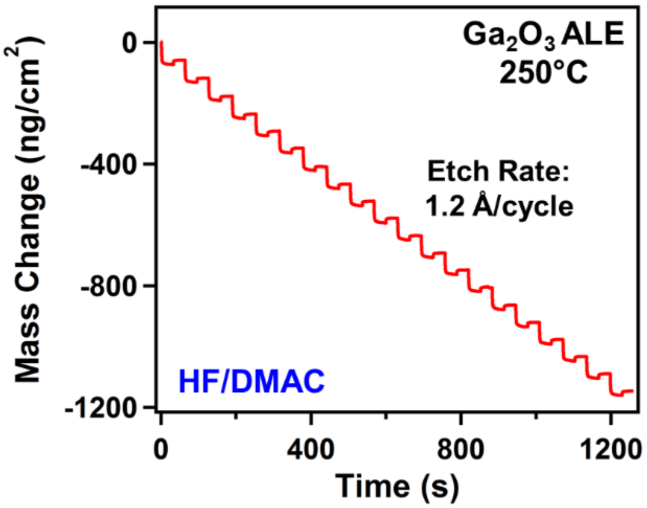

Figure 2. Quartz crystal microbalance measurements of mass change of Ga_2O_3 ALD film versus time during sequential HF and dimethylaluminum chloride (DMAC) exposures at 250°C.